

Circuit- and System-Driven Requirements for Digital Logic Devices

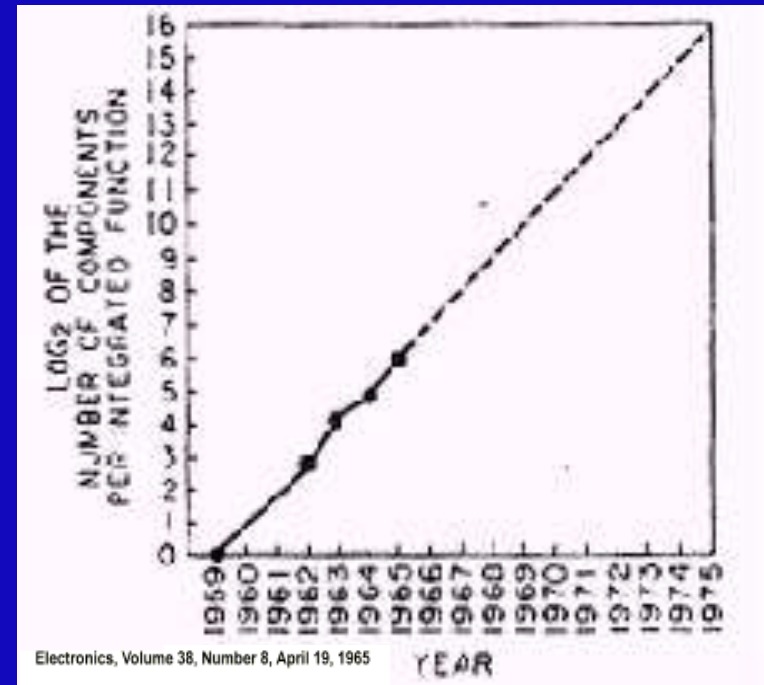
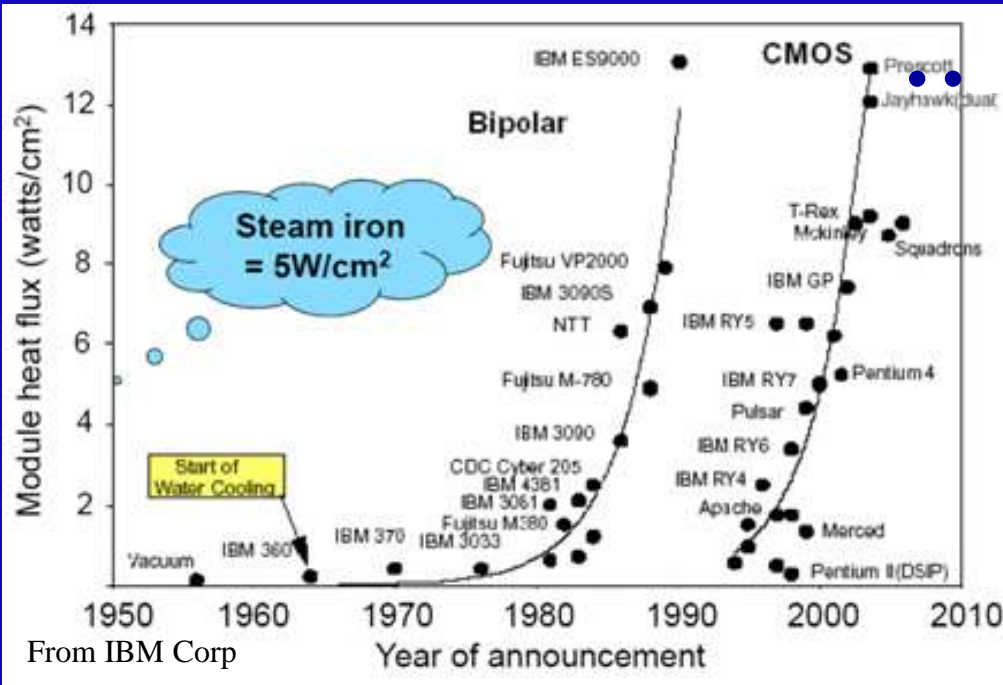
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A Reminder

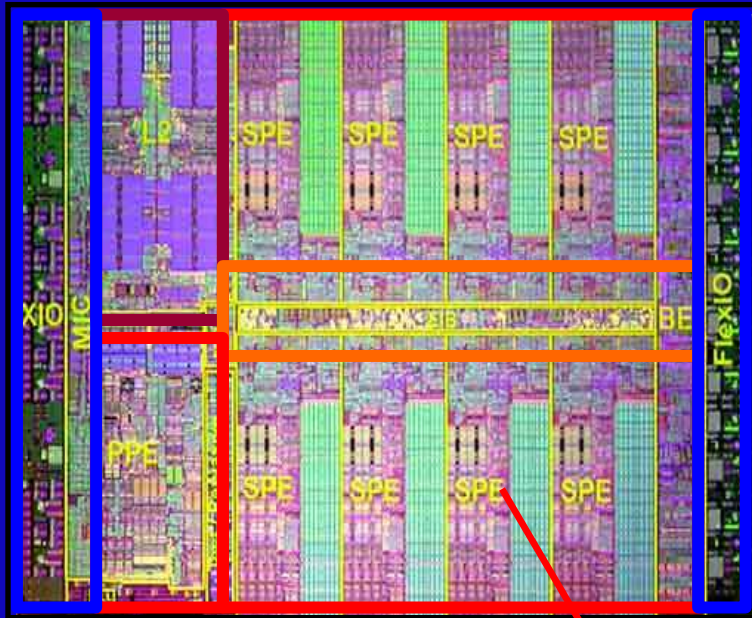


- CMOS has hit the power wall
 - Non-scaling of kT/q and hence V_{dd} , V_{th}
- But, can't forget that **reducing cost** is still the underlying imperative

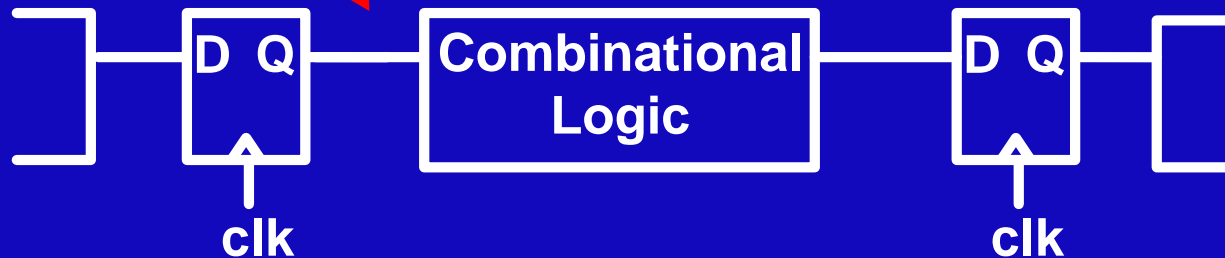
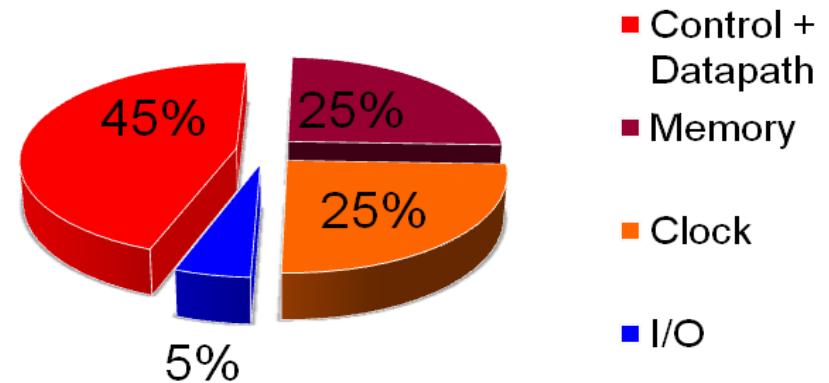
My Assumptions (Implied by Cost)

- Stick to binary digital logic
 - Replacing full design/software stack generally too expensive
 - Devices need to have gain (noise margins)
- New device has yield and reliability comparable to CMOS
 - Today: chip with ~5 billion devices works for ~5 years
- New device has lower **circuit/system-level** energy over some range of performance and area...
 - Can translate all of these back to \$

What Digital Chips Look Like



Typical Processor Power Breakdown

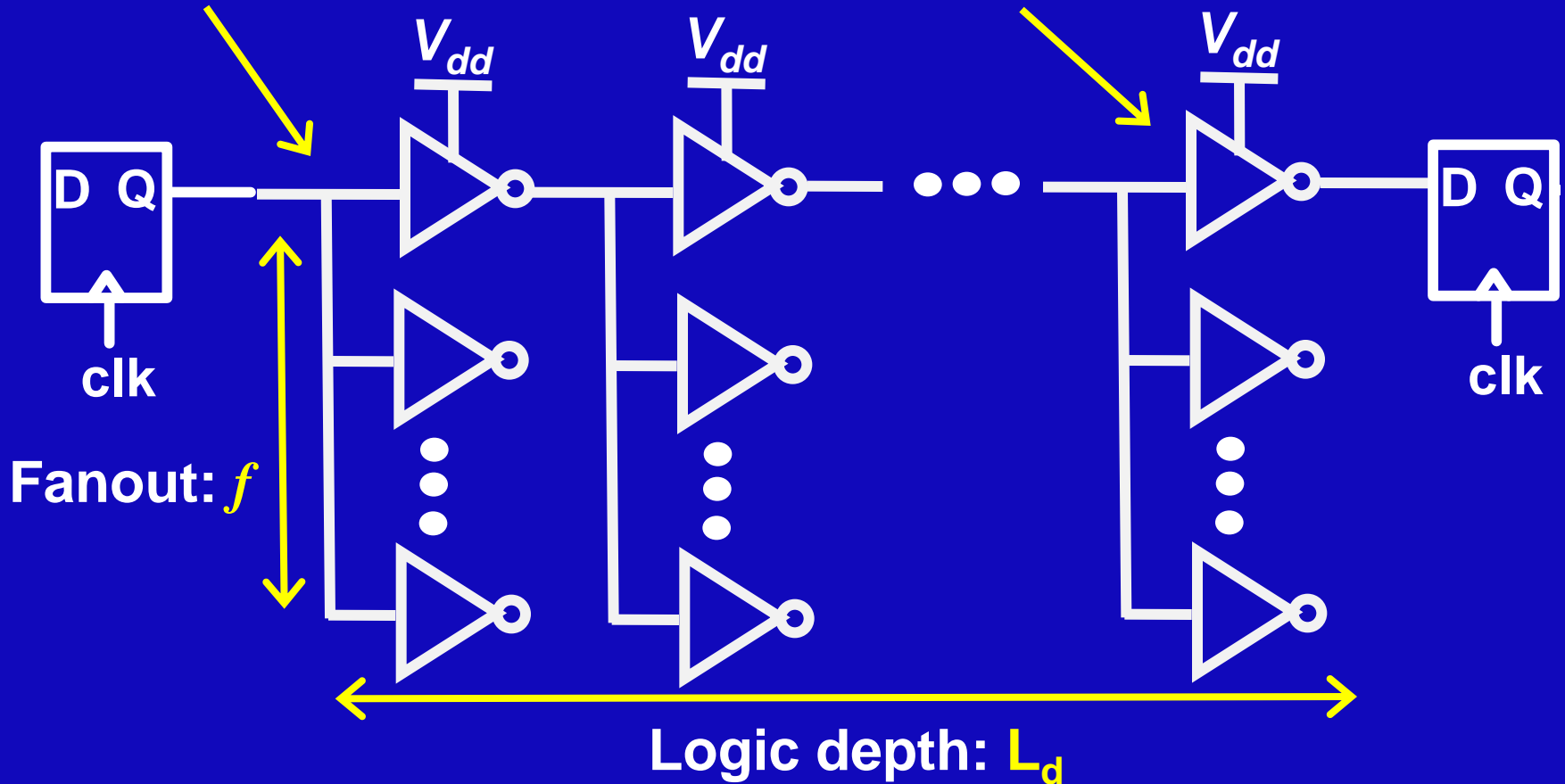


- Chip energy/perf. tracks datapath/control
- Clock frequency set by delay through CL

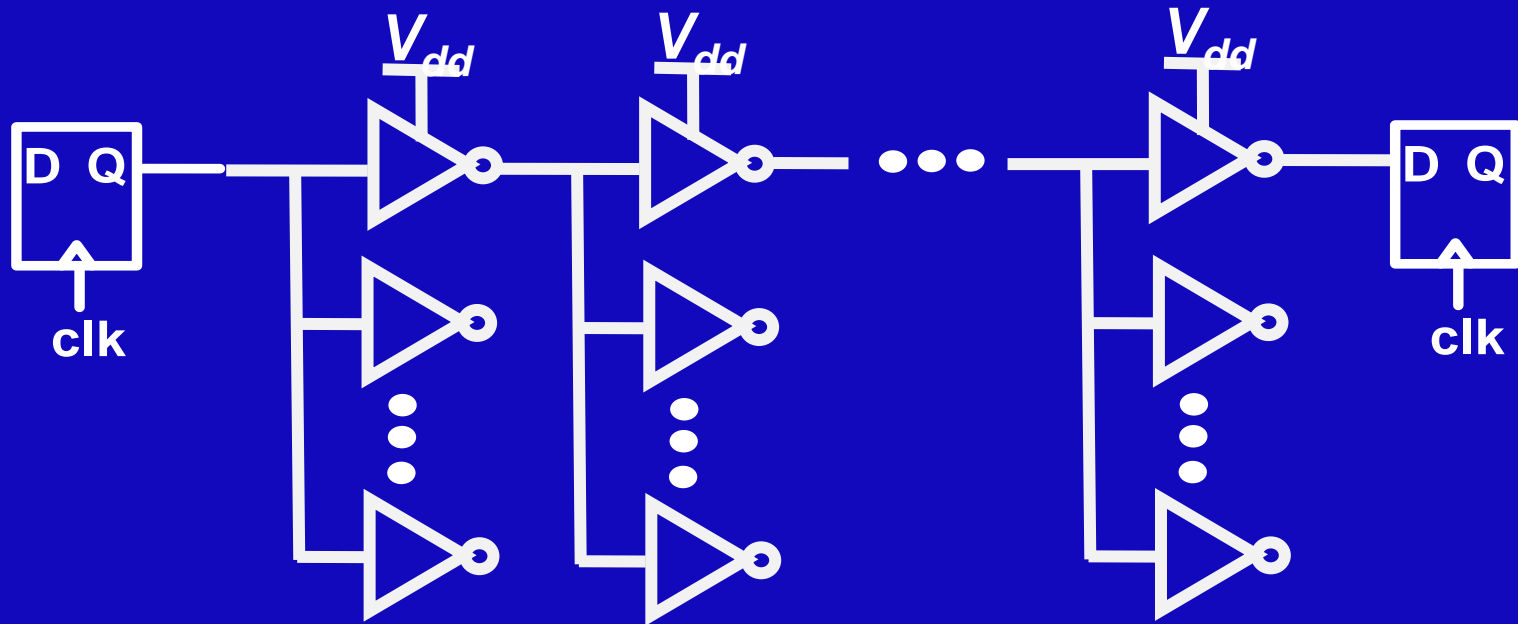
Logic Energy and Delay

Activity factor: α

Cap./inv.: C

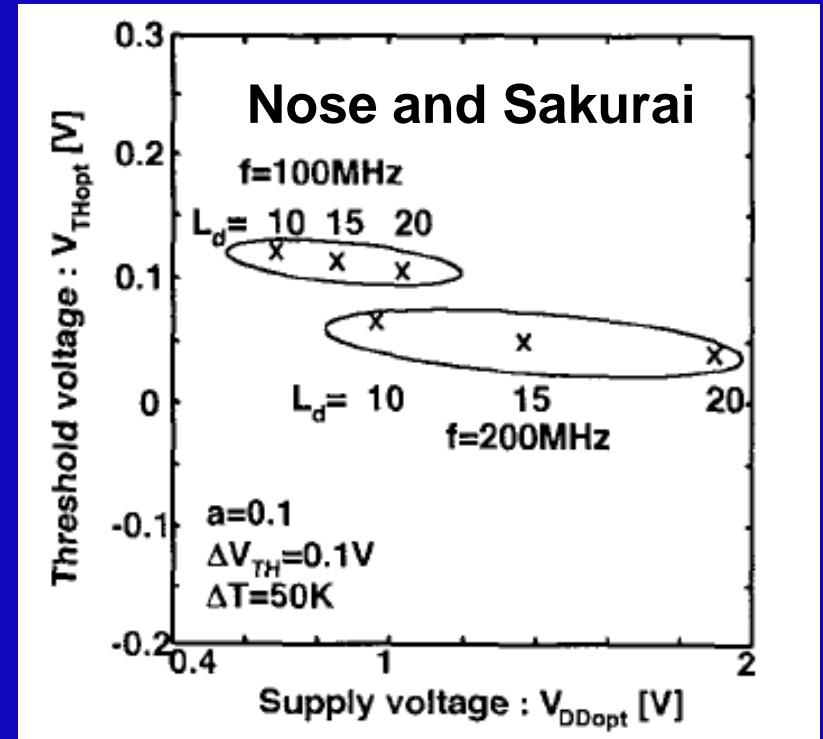
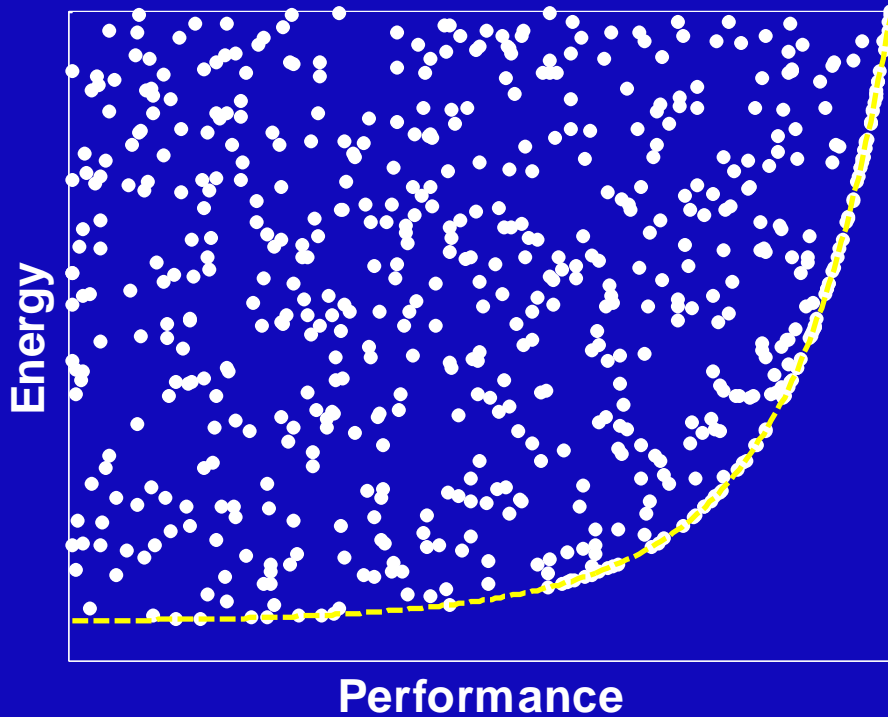


Logic Energy and Delay



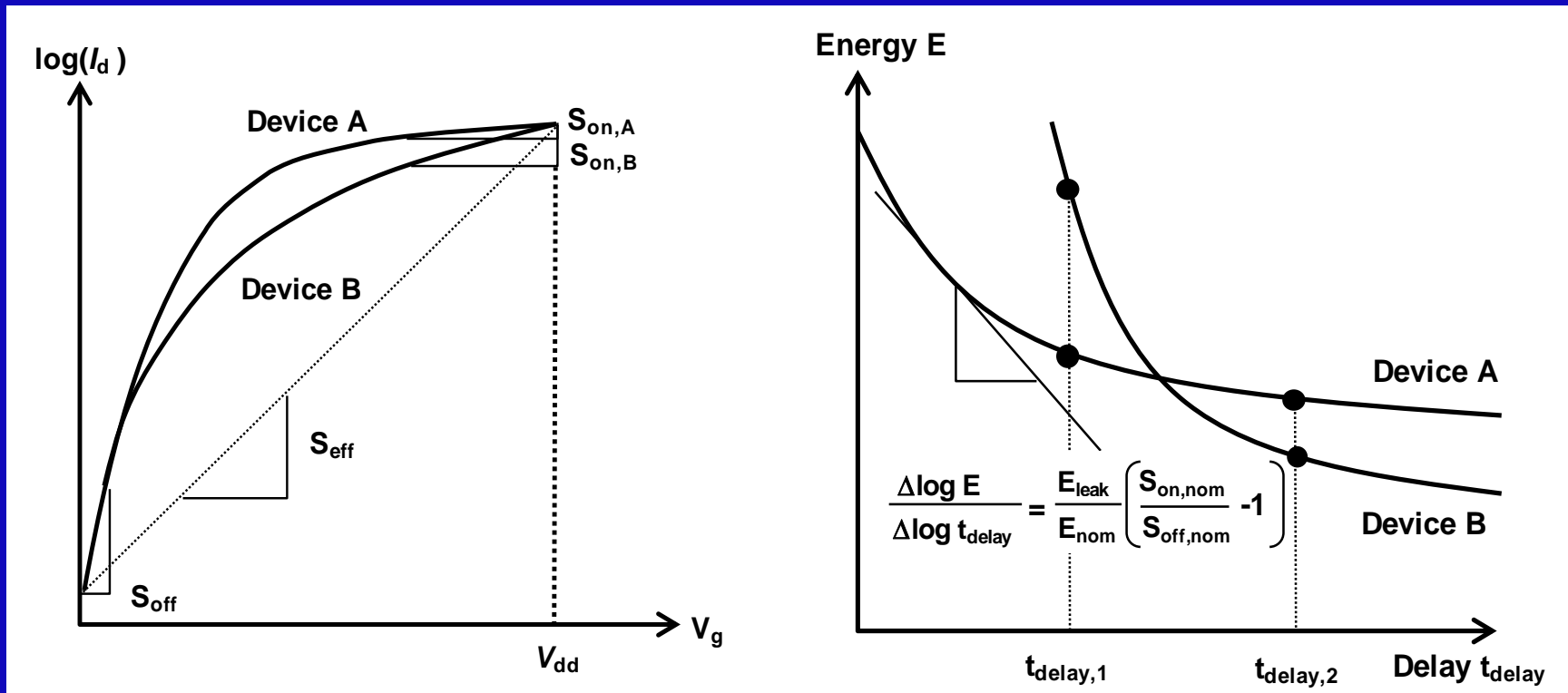
- $t_{\text{delay}} = L_d f C V_{dd} / (2I_{\text{on}})$
- $E_{\text{dyn}} + E_{\text{leak}} = \alpha L_d f C V_{dd}^2 + L_d f I_{\text{off}} V_{dd} t_{\text{delay}}$
- $E_{\text{dyn}} + E_{\text{leak}} = \alpha L_d f C V_{dd}^2 (1 + (L_d f / 2\alpha) / (I_{\text{on}} / I_{\text{off}}))$

Implications on Required I_{on}/I_{off}



- Pick V_{dd} , V_{th} to minimize energy for given performance (1/delay)
 - Assuming work function (V_{th}) can be freely tuned
- Result: **optimal $I_{on}/I_{off} \propto L_d \cdot f / \alpha$**

Optimal I_{on}/I_{off} Insensitive to Device



$$\frac{I_{on}}{I_{off}} = \beta \frac{L_d f}{4\alpha}, \quad \beta = -\frac{S_{eff}}{S_{off}} \text{lambertW} \left(-\frac{4\alpha}{L_d f} \frac{S_{off}}{S_{eff}} e^{\left(\frac{S_{off} + S_{on}}{S_{eff}} \right)} \right)$$

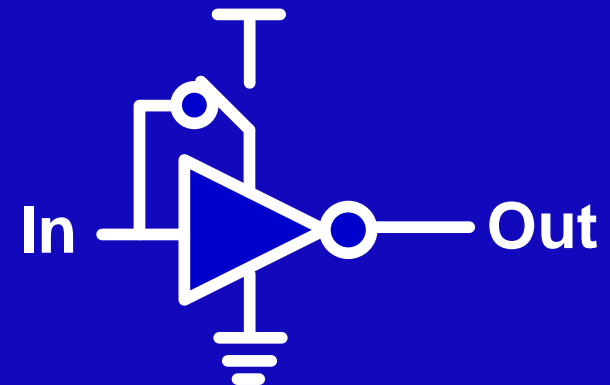
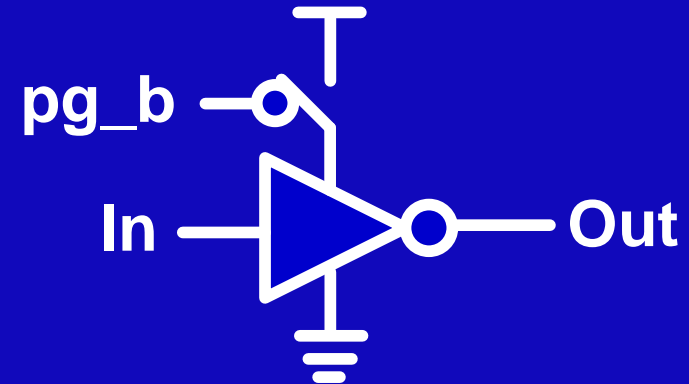
H. Kam, T.-J. King Liu, and E. Alon, "Design Requirements for Steeply Switching Logic Devices," to appear in *IEEE Trans. on Electron Devices*

Example Numbers

- **Logic depth: $L_d \sim 20$ to 40**
 - Can't be too small b/c of flip-flop and clocking overhead
- **Activity factor: $\alpha \sim 1\%$ to .01%**
 - Most outputs unlikely to change in complex logic
- **Fanout: $f \sim 2$ to 6**
- **So optimal $I_{on}/I_{off} \sim 10^4 - 10^6$**
 - This is really the logic switch requirement
 - I.e., power management doesn't change this...

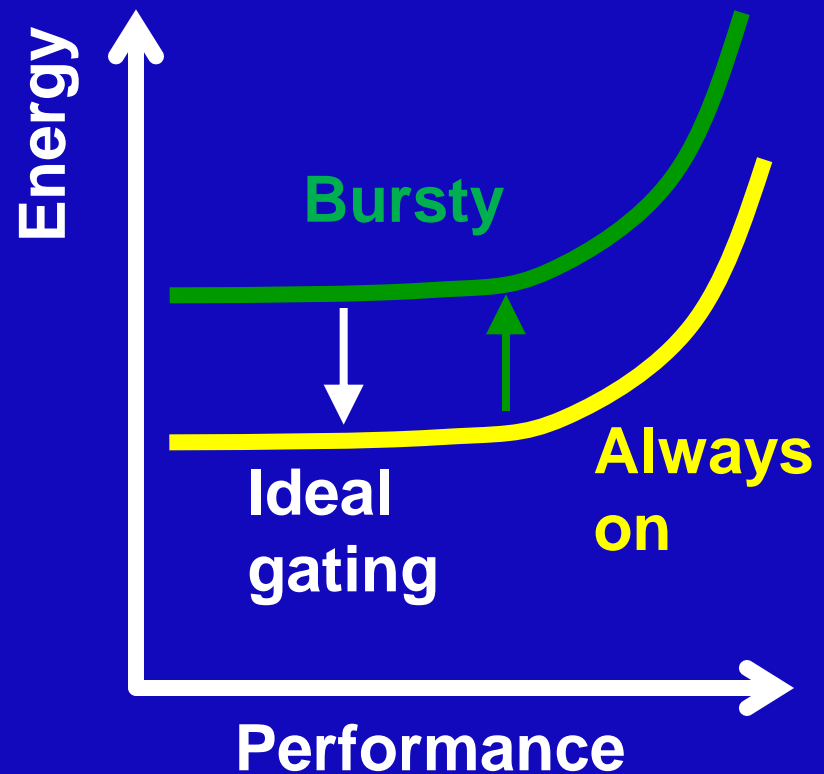
Why Power Gating Doesn't Help

- Can indeed use another switch to turn off power
 - With higher I_{on}/I_{off} power switch, reduces E_{leak}
- But very hard to improve effective α
 - When to turn the power on?
- “Power managing” each gate = reproducing the logic...

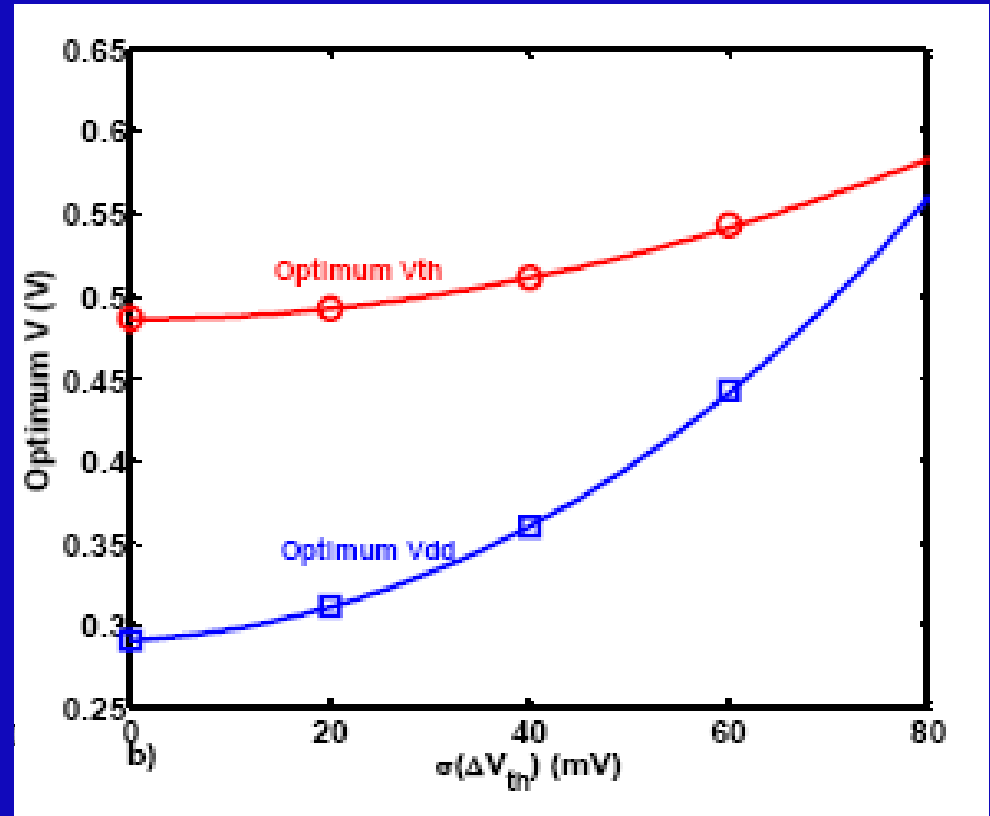
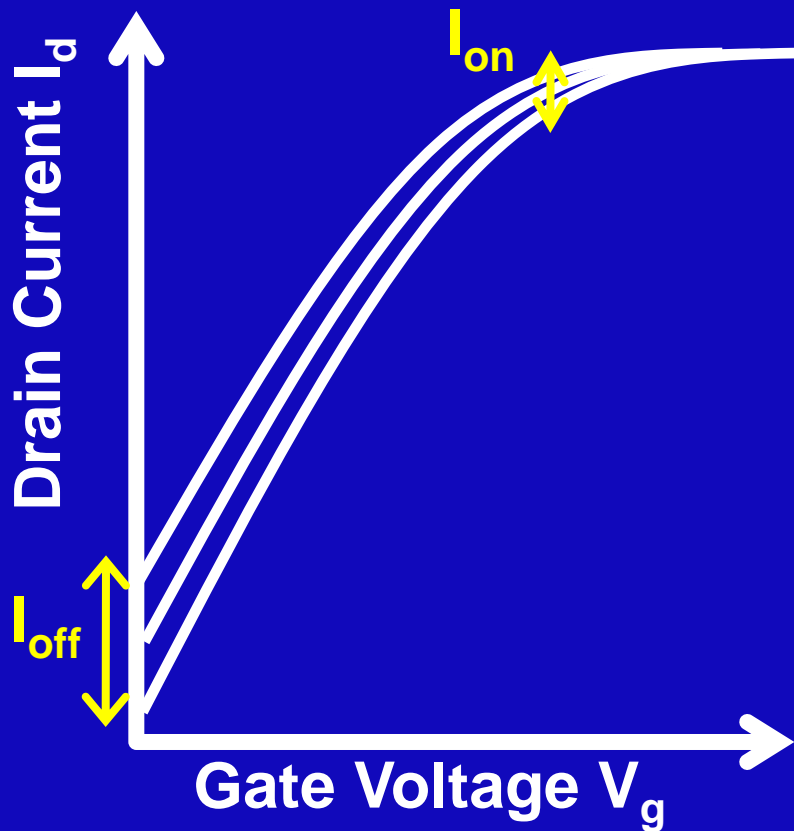


What Power Gating Is Good For

- Eliminate E_{leak} when **system** is off
 - I.e., when “obviously” not doing any work
 - So that knowing gating signal is nearly free
- Key point:
 - Power gating only reduces “system variability” penalty
 - Device variability?



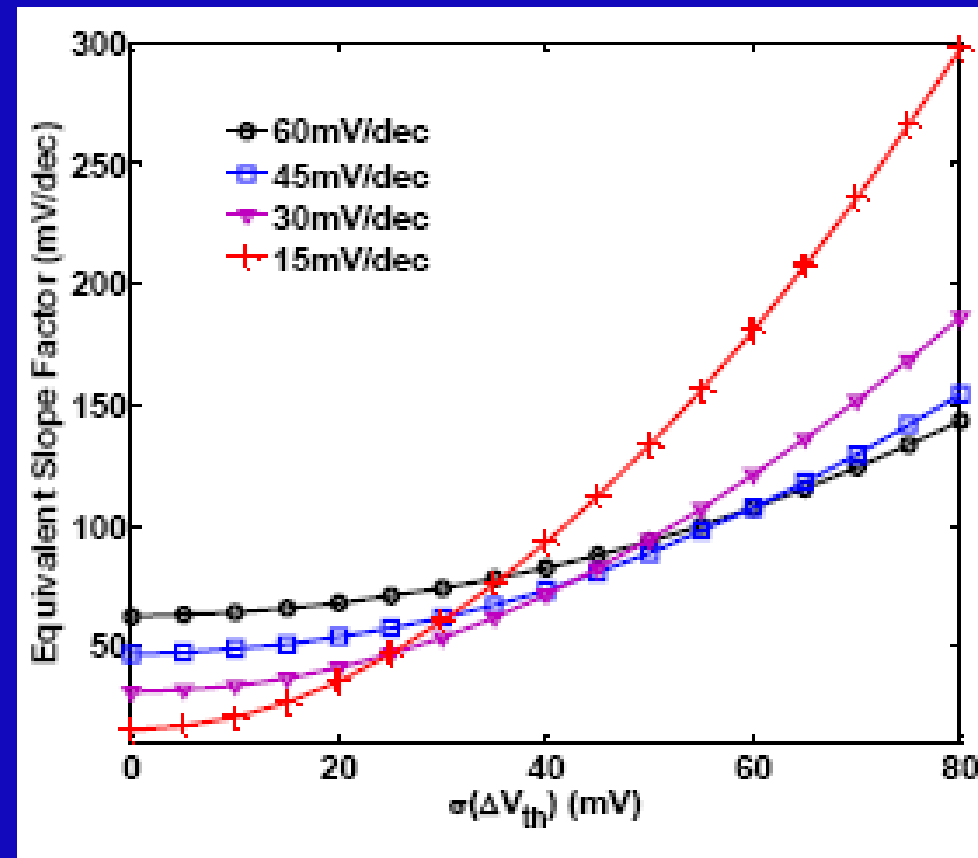
Implications of Device Variability



- Device variability hurts in two ways
 - Reduces effective I_{on} (delay set by worst-case)
 - Increase effective I_{off} (leaky devices dominate)
- Forces increase in nominal I_{on}/I_{off} ...

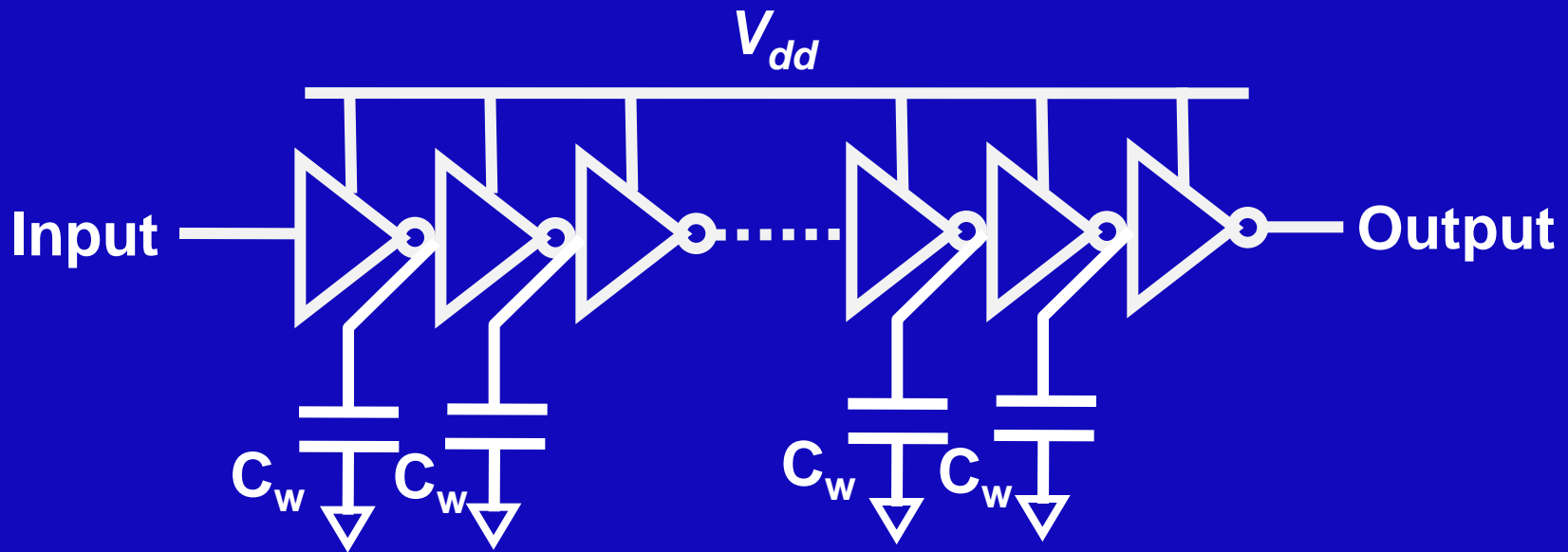
Steep Switches Need Low Variation

- With steep device, leakage increases dramatically with $\sigma(\Delta V_{th})$
- For same variability:
 - Can even make “steep” switch worse than CMOS



- Must consider and quantify device variability in advance

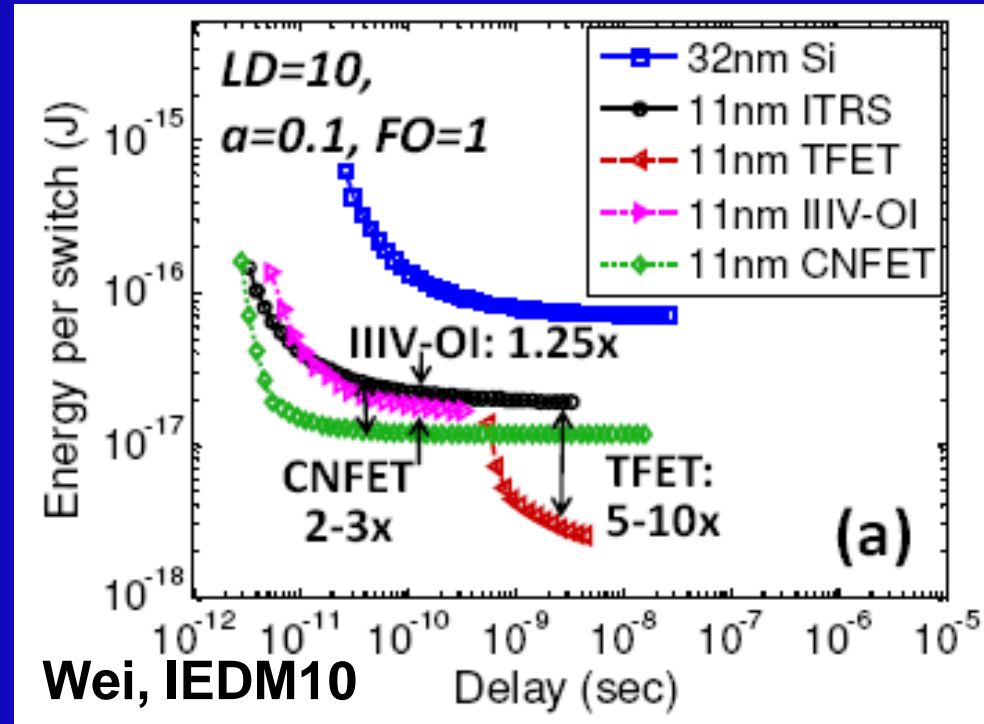
Another Issue: Wire Capacitance



- **Wires critical to both delay and energy:**
 - Minimum device C: **~ 0.1 fF**
 - $1\mu\text{m}$ wire C: **~ 0.2 fF**
- **Wires often set required device V_{dd}/I_{on} (R_{on})**

Where New Devices Look Good

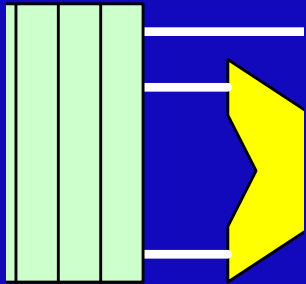
- Achieving sharp S^{-1} and low R_{on} looks really tough



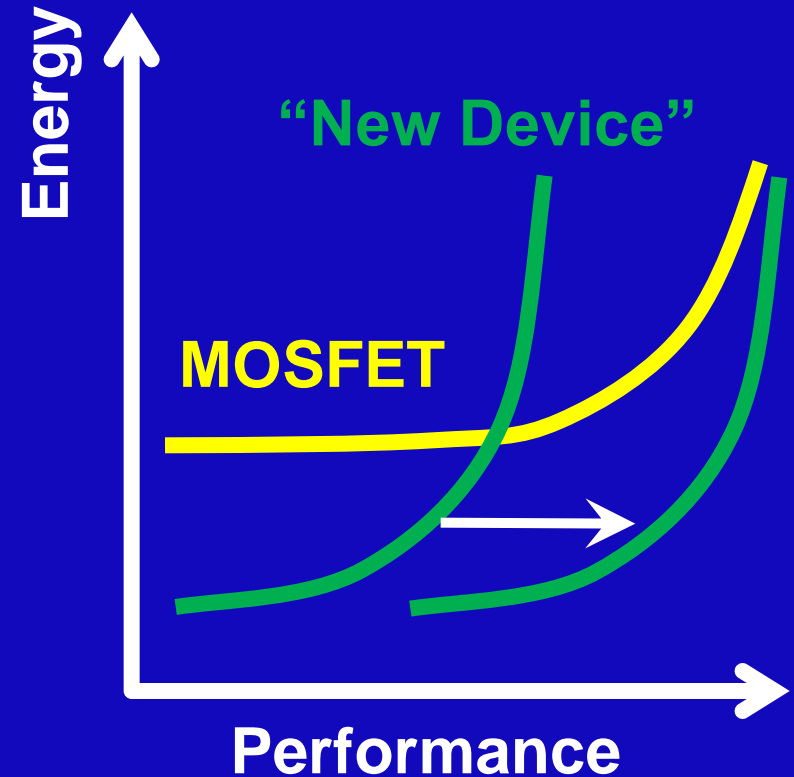
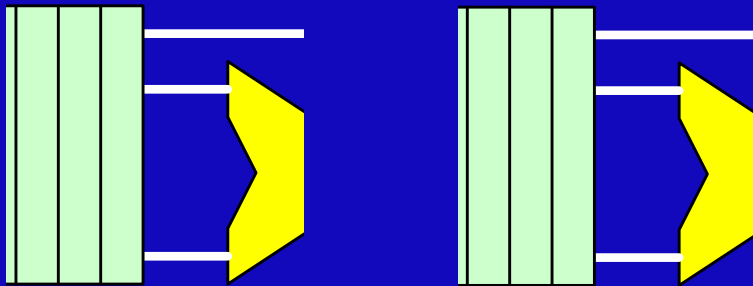
- But, even if new switch only improves energy at higher delay (higher R_{on})...

Parallelism

Perf. $\propto f_{clk}$



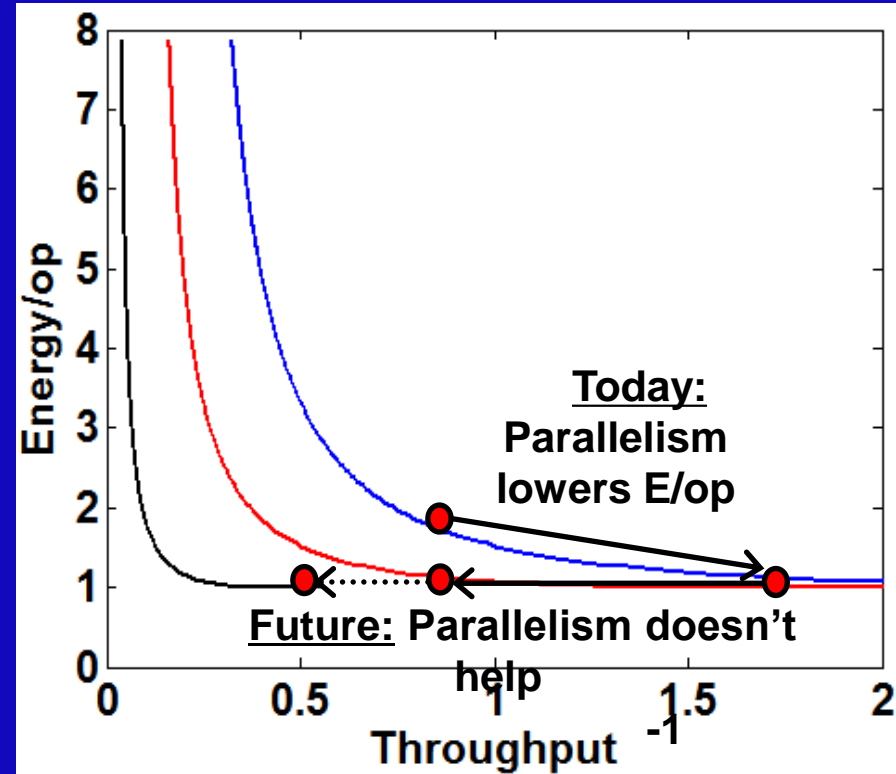
Perf. $\propto 2f_{clk}$, E/op \sim const



- **Parallelism allows slower devices**
 - Already applying parallelism to CMOS today

Parallelism (cont'd)

- Benefits of parallelism will eventually run out
 - CMOS has minimum energy/op
 - Set by min. V_{dd} to achieve optimal I_{on}/I_{off}



- Likely the main opportunity for new devices...
 - If achieve I_{on}/I_{off} of $\sim 10^4 - 10^6$ at ($>10X$) lower $C_{tot} V_{dd}^2$

Summary

- **Simple circuit/system models set device requirements**
 - $I_{\text{on}}/I_{\text{off}}$ set by logic depth, activity factor
 - Must consider variability and wires
- **Parallelism limited by device E_{min}**
 - Opportunity for new, low voltage devices
- **Final plug: device/circuit co-design critical**
 - Especially if alternate logic device is very different from CMOS

Acknowledgements

- **NSF Center for E3S**
- **Berkeley Wireless Research Center**
- **DARPA**
- **FCRP**